

2N2608, 2N2609

P-Channel Silicon Junction Field-Effect Transistor

- Low-Level Choppers
- Data Switches
- Commutators

Absolute maximum ratings at T_A = 25°C

Reverse Gate Source & Gate Drain Voltage	-30V
Continuous Forward Gate Current	50 mA
Continuous Device Power Dissipation	300 mW
Power Derating	2 mW/°C
Storage Temperature Range	-65°C to +150°C

At 25°C free air temperature		2N2608		2N2609		Process PJ32	
		Min	Max	Min	Max	Unit	Test Conditions
Gate Source Breakdown Voltage	V _{(BR)GSS}	-30		-30		V	I _G = -1 uA, V _{DS} = 0 V
Gate Reverse Current	I _{GSS}		10		30	nA	V _{GS} = 10 V, V _{DS} = 0 V
Gate Source Cutoff Voltage	V _{GS(OFF)}	1	4	1	4	V	V _{DS} = -10 V, V _{GS} = 0 V
Drain Saturation Current (pulsed)	I _{DSS}	-0.9	-4.5	-2	-10	mA	V _{DS} = -10 V, V _{GS} = 0 V

Dynamic Electrical Characteristics

Common-Source Forward Transconductance	g _{fs}	1		25		mS	V _{DS} = -10 V, V _{GS} = 0 V	f = 1 kHz
Common-Source Input Capacitance	C _{iss}		17		30	pF	V _{DS} = -10 V, V _{GS} = 1 V	f = 1 MHz
Common-Source Reverse Transfer Capacitance	C _{rss}		5		7	pF	V _{DS} = 10 V, I _D = 5 mA	f = 1 MHz

Typical

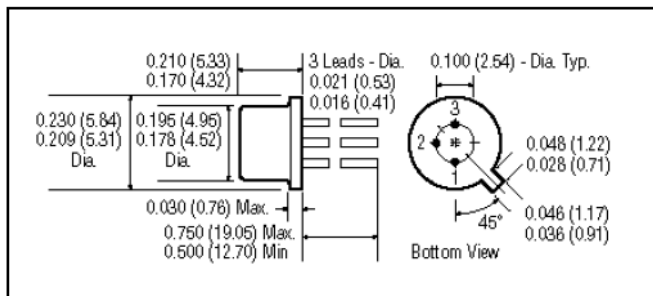
Equivalent Short Circuit Input Noise Voltage	~e _N	10		10		nV/√Hz	V _{DS} = 10 V, I _D = 5 mA	f = 1 kHz
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TO-18 Package

Dimensions in Inches (mm)

Pin Configuration

1 Source 1, 2 Gate & Case, 3 Drain



Surface Mount - SMP2608, SMP2609



715 N. Glenville Dr., Ste. 400
 Richardson, TX 75089
 (972) 238-9700 Fax (972) 238-5338

www.interfet.com